

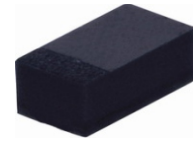
SMD Schottky Barrier Diode



SMD Diodes Specialist

CDBFR0240(RoHs Device)

$I_o = 200 \text{ mA}$
 $V_R = 40 \text{ Volts}$

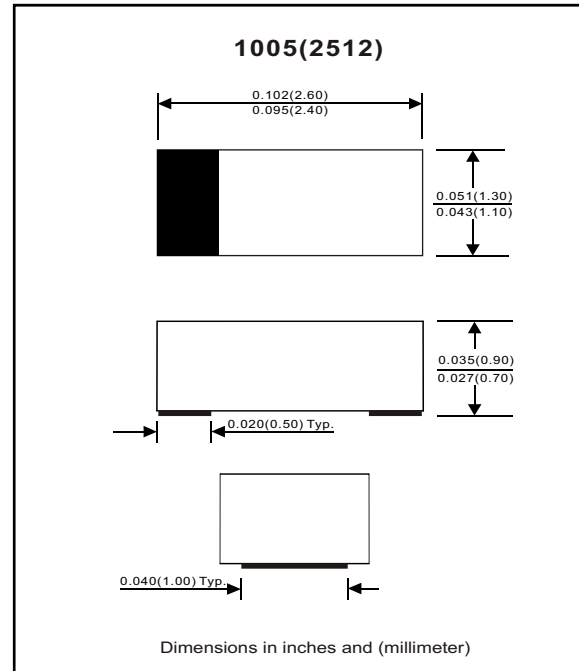


Features

- Designed for mounting on small surface.
- Extremely thin/leadless package.
- Majority carrier conduction.

Mechanical data

- Case: 1005(2512) standard package, molded plastic.
- Terminals: Gold plated, solderable per MIL-STD-750, method 2026.
- Polarity: Indicated by cathode band.
- Mounting position: Any
- Weight: 0.006 gram(approx.).



Maximum Rating (at TA=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Repetitive peak reverse voltage		V_{RRM}			45	V
Reverse voltage		V_R			40	V
Average forward current		I_o			200	mA
Forward current, surge peak	8.3 ms single half sine-wave superimposed on rate load (JEDEC method)	I_{FSM}		2000		mA
Power Dissipation		P_D			150	mW
Storage temperature		T_{STG}	-40		+125	°C
Junction temperature		T_j			+125	°C

Electrical Characteristics (at TA=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 200 \text{ mA DC}$	V_F		0.45	0.55	V
Reverse current	$V_R = 30 \text{ V}$	I_R		1	10	uA
Capacitance between terminals	$F = 1 \text{ MHz}$ and 10 VDC reverse voltage	C_T		9		pF

RATING AND CHARACTERISTIC CURVES (CDBFR0240)

Fig. 1 - Forward characteristics

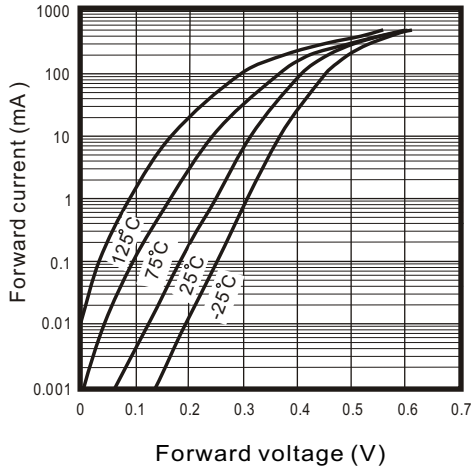


Fig. 2 - Reverse characteristics

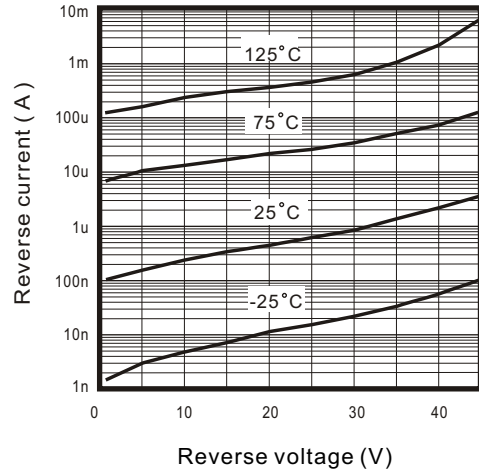


Fig. 3 - Capacitance between terminals characteristics

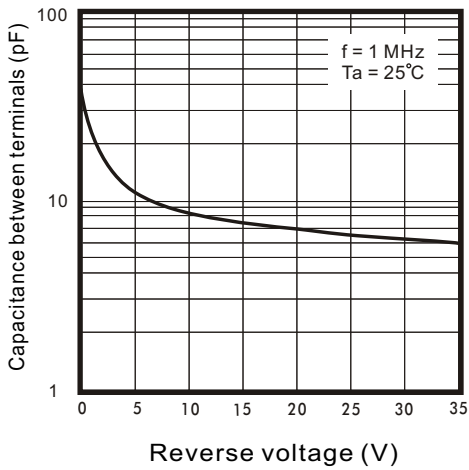


Fig. 4 - Current derating curve

